

# 2SA2166-T150

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE

AEC-Q101 Compliance

## DESCRIPTION

2SA2166 is a silicon PNP epitaxial type transistor designed with high collector current, low  $V_{CE(sat)}$ .

## FEATURE

- High collector current

$$I_{C(MAX)} = -500\text{mA}$$

- Low collector to emitter saturation voltage

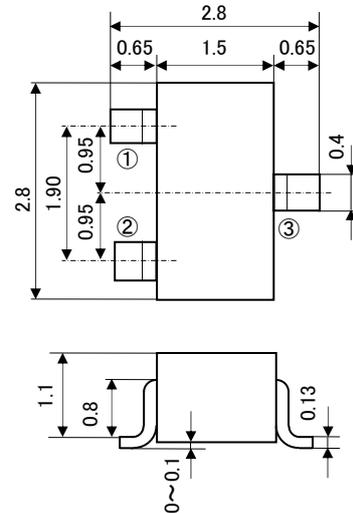
$$V_{CE(sat)} < -0.4V_{max} (I_C = -150\text{mA} / I_B = -15\text{mA})$$

## APPLICATION

For switching application, small type motor drive application.

## OUTLINE DRAWING

Unit: mm



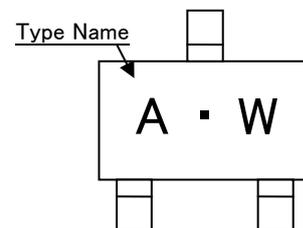
## TERMINAL CONNECTOR

- ①: BASE                      EIAJ: SC-59  
②: EMITTER                JEDEC: Similar to  
③: COLLECTOR            TO-236

## MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

記号	項目	定格値	単位
$V_{CEO}$	Collector to Emitter voltage	-60	V
$V_{CBO}$	Collector to Base voltage	-60	V
$V_{EBO}$	Emitter to Base voltage	-5	V
$I_C$	Collector current	-500	mA
$P_C$	Collector dissipation	200	mW
$T_j$	Junction temperature	+150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~+150	$^\circ\text{C}$

## MARKING



## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

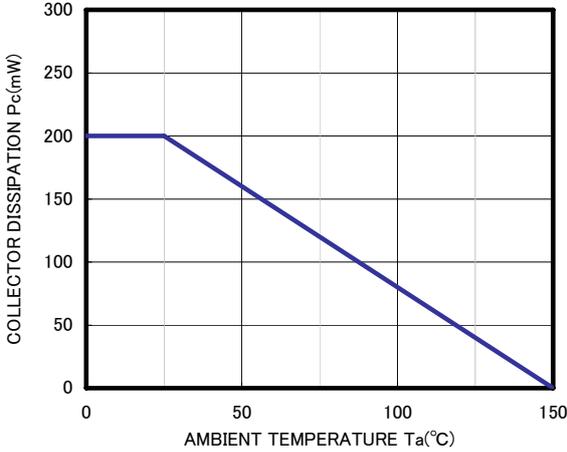
Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E breakdown voltage	$I_C = -1\text{mA}, I_B = 0$	-60	—	—	V
$V_{(BR)CBO}$	C to B breakdown voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60	—	—	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5	—	—	V
$I_{CBO}$	Collector cut off current	$V_{CB} = -50\text{V}, I_E = 0$	—	—	-0.1	$\mu\text{A}$
$I_{EBO}$	Emitter cut off current	$V_{EB} = -3\text{V}, I_C = 0$	—	—	-0.1	$\mu\text{A}$
$h_{FE}$	DC forward current gain	$I_C = -150\text{mA}, V_{CE} = -10\text{V}$	100	—	300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$	—	—	-0.4	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$	—	—	-1.3	V
$f_T$	Gain band width product	$I_E = 50\text{mA}, V_{CE} = -20\text{V}, f = 100\text{MHz}$	200	—	—	MHz
$C_{ob}$	Collector output capacitance	$V_{CB} = -10\text{V}, f = 1\text{MHz}$	—	—	8	pF

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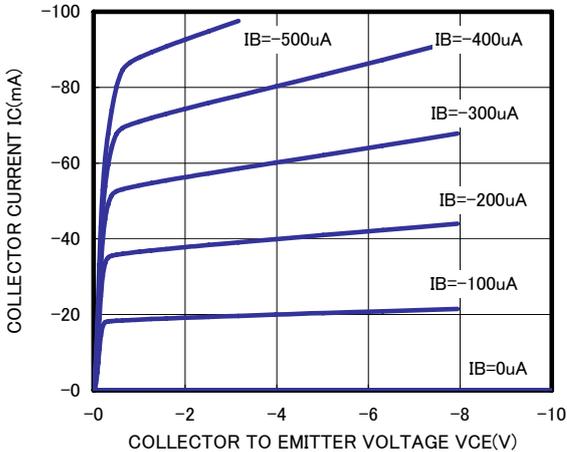
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## TYPICAL CHARACTERISTICS

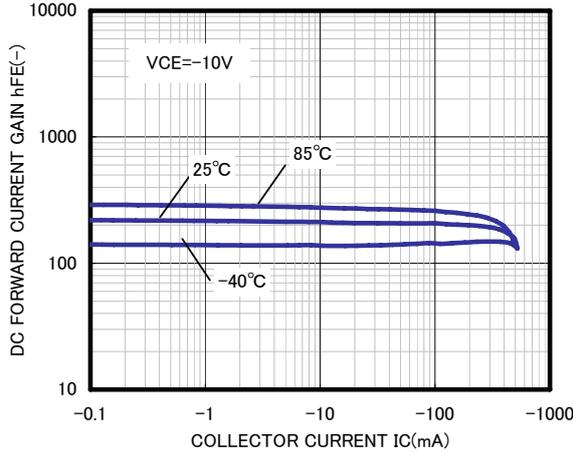
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



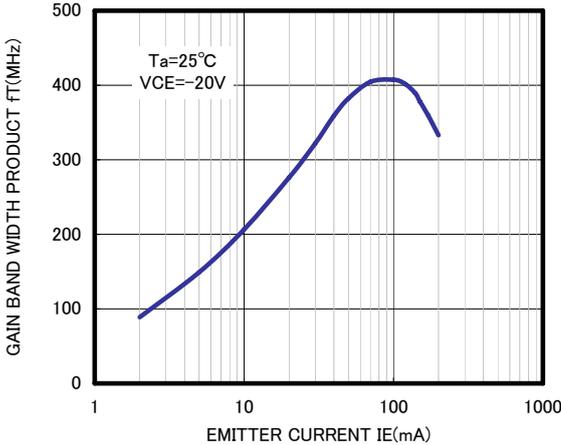
COMMON EMITTER OUTPUT  $T_a=25^\circ\text{C}$



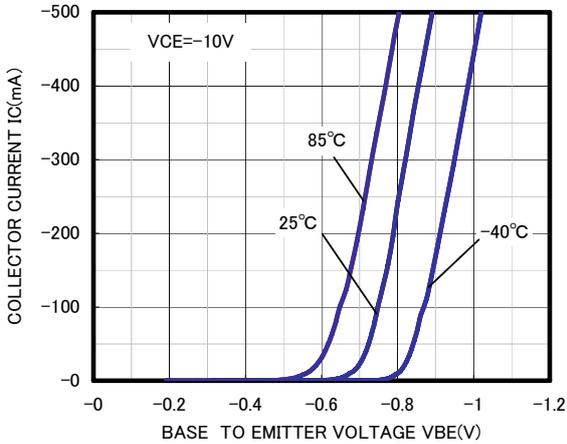
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



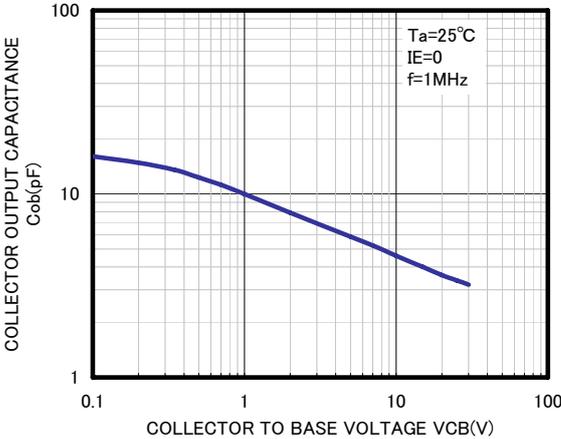
GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



COMMON EMITTER TRANSFER



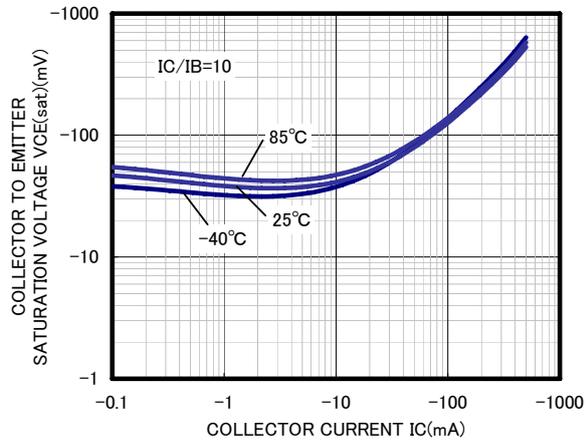
COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



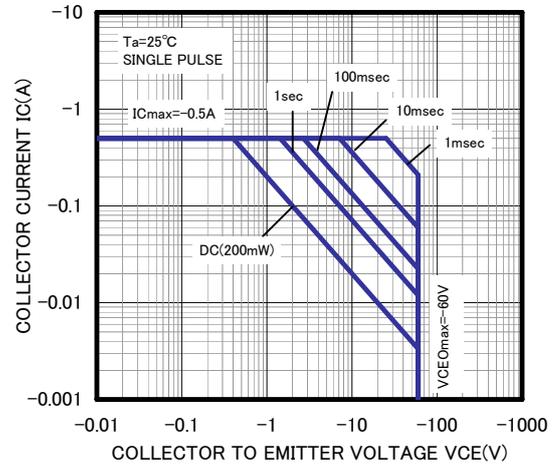
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COLLECTOR TO EMITTER SATURATION VOLTAGE  
VS. COLLECTOR CURRENT



AREA OF SAFE OPERATION





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